

◆ Features:

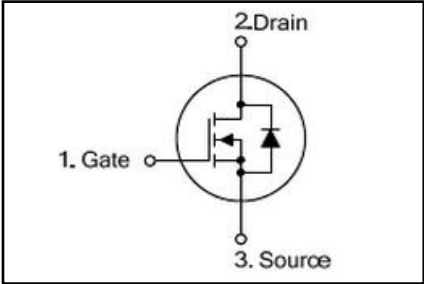
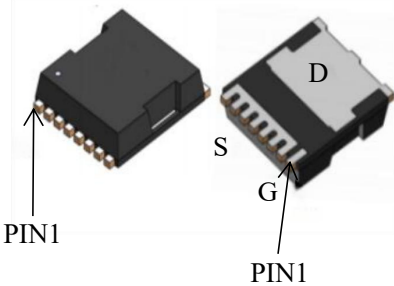
- ✧ Fast switching speed
开关速度快
- ✧ Low gate charge
低门充电
- ✧ High power and current handling capability
高功率和电流处理能力
- ✧ RoHS compliant
符合 RoHS 标准

◆ Applications

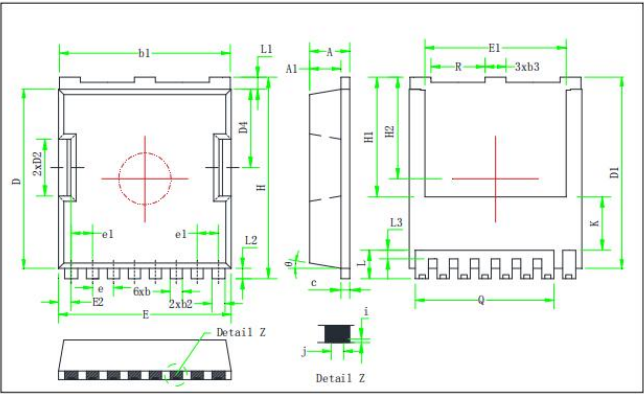
- ✧ DC to DC converters
直流到直流转换
- ✧ Synchronous Rectification
同步整流



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Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	2.25	2.30	2.35	E2	0.65	0.70	0.75
A1	1.75	1.80	1.85	H	11.60	11.70	11.80
b	0.65	0.70	0.75	H1	6.95 BSC		
b1	9.75	9.80	9.85	H2	5.90 BSC		
b2	0.70	0.75	0.80	i	0.10 REF		
b3	1.15	1.20	1.25	j	0.35 REF		
c	0.45	0.50	0.55	K	3.10 REF		
D	10.35	10.40	10.45	L	1.55	1.65	1.75
D1	11.00	11.10	11.20	L1	0.65	0.70	0.75
D2	3.25	3.30	3.35	L2	0.50	0.60	0.70
D4	4.50	4.55	4.60	L3	0.40	0.50	0.60
e	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC			R	3.05	3.10	3.15
E	9.85	9.90	9.95	theta	10°REF		
E1	8.00	8.10	8.20				

◆ Absolute Maximum Ratings (Tc=25°C)

Symbol	Parameters	Ratings	Unit
V _{DSS}	Drain-Source Voltage 漏源电压	100	V
V _{GS}	Gate-Source Voltage-Continuous 栅源电压	±20	V
I _D	Drain Current-Continuous (Note 2) 漏极持续电流	300	A
I _{DM}	Drain Current-Single Plused (Note 1) 漏极单次脉冲电流	1200	A
P _D	Power Dissipation (Note 2) 功率损耗	400	W
T _j	Max.Operating junction temperature 最大结温	150	°C

◆ Electrical characteristics (Tc=25°C unless otherwise noted)

Symbo l	Parameters	Min	Typ	Max	Units	Conditions
Static Characteristics						
B _{VDSS}	Drain-Source Breakdown VoltageCurrent (Note 1) 漏极击穿电压	100	--	--	V	I _D =250μA, V _{GS} =0V
V _{GS(th)}	Gate Threshold Voltage 栅极开启电压	2.0	--	4.0	V	V _{DS} =V _{GS} , I _D =250μA
R _{DS(on)}	Drain-Source On-Resistance 漏源导通电阻	--	1.9	--	mΩ	V _{GS} =10V, I _D =30A
I _{GSS}	Gate-Body Leakage Current 栅极漏电流	--	--	±100	nA	V _{GS} =±25V, V _{DS} =0
I _{DSS}	Zero Gate Voltage Drain Current 零栅极电压漏极电流	--	--	1	μA	V _{DS} =100V, V _{GS} =0
g _{fs}	Forward Transconductance 正向跨导	--	55	--	S	V _{DS} =10V, I _D =50A

**OSC300N10G****N-Channel Power Trench MOSFET®**

Switching Characteristics						
T _{d (on)}	Turn-On Delay Time 开启延迟时间	--	55	--	ns	V _{DD} =50V, I _D =30A, R _G =5Ω
T _r	Rise Time 上升时间	--	30	--	ns	
T _{d (off)}	Turn-Off Delay Time 关闭延迟时间	--	165	--	ns	
T _f	Fall Time 下降时间	--	50	--	ns	
Q _g	Total Gate Charge 栅极总电荷	--	150	--	nC	V _{DS} =50V V _{GS} =10V, I _D =30A
Q _{gs}	Gate-Source Charge 栅源极电荷	--	25	--	nC	
Q _{gd}	Gate-Drain Charge 栅漏极电荷	--	40	--	nC	
Dynamic Characteristics						
C _{iss}	Input Capacitance 输入电容	--	12.5	--	nF	V _{DS} =25V, V _{GS} =0, f=1MHz
C _{oss}	Output Capacitance 输出电容	--	920	--	pF	
C _{rss}	Reverse Transfer Capacitance 反向传输电容	--	35	--	pF	
I _S	Continuous Drain-Source Diode Forward Current (Note 2) 二极管导通正向持续电流	--	--	300	A	
V _{SD}	Diode Forward On-Voltage 二极管正向导通电压	--	--	1.0	V	I _S =30A, V _{GS} =0
R _{th(j-c)}	Thermal Resistance, Junction to Case 结到外壳的热阻	--	--	0.31	°C/W	